

IN THE ABSTRACT:

Please cancel prior Abstract and insert the following:

--A method of manufacturing a MOS-type solid-state image pickup device having a photoelectric conversion unit, a transfer MOS transistor, a gate electrode disposed on an insulating film and a semiconductor substrate on which the photoelectric conversion unit and the transfer MOS transistor are disposed, includes a first step of forming a second semiconductor region by ion implanting an impurity of a second conductivity type at a first angle with a first energy using the gate electrode as a mask, and a second step of forming a fifth semiconductor region by ion implanting an impurity of the second conductivity type at a second angle with a second energy using the gate electrode as a mask. A fourth semiconductor region is formed by ion implanting an impurity of the second conductivity type. The second energy is smaller than the first energy, and the first and second angles are respectively angles to a direction normal to a surface of the semiconductor substrate, with the second angle being larger than the first angle, and the first and third steps being performed separately.--